4V Drive Nch MOSFET

RSF014N03

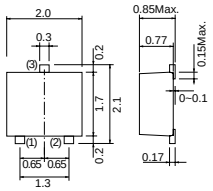
●Structure
Silicon N-channel MOSFET

●Features
1) Low On-resistance.
2) Space saving, small surface mount package (TUMT3).
3) 4V drive.

●Applications
Switching

●Dimensions (Unit : mm)

TUMT3



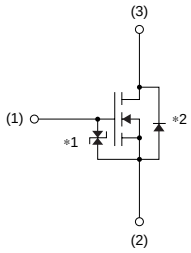
(1) Gate
(2) Source
(3) Drain

Abbreviated symbol : PN

●Packaging specifications

Type	Package	Taping
	Code	TL
	Basic ordering unit (pieces)	3000
RSF014N03		○

●Inner circuit



*1 ESD PROTECTION DIODE
*2 BODY DIODE

(1) Gate
(2) Source
(3) Drain

●Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit
Drain-source voltage		V_{DSS}	30	V
Gate-source voltage		V_{GSS}	20	V
Drain current	Continuous	I_D	±1.4	A
	Pulsed	I_{DP} *1	±5.6	A
Source current (Body diode)	Continuous	I_S	0.6	A
	Pulsed	I_{SP} *1	5.6	A
Total power dissipation		P_D *2	0.8	W
Channel temperature		Tch	150	°C
Range of storage temperature		Tstg	−55 to +150	°C

*1 Pw≤10μs, Duty cycle≤1%
*2 Mounted on a ceramic board

●Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	Rth(ch-a) *	156	°C/W

* Mounted on a ceramic board

●**Electrical characteristics** (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	–	–	10	μA	V_{GS}=20V, V_{DS}=0V
Drain-source breakdown voltage	$V_{(BR)\ DSS}$	30	–	–	V	I_D= 1mA, V_{GS}=0V
Zero gate voltage drain current	I_{DSS}	–	–	1	μA	V_{DS}= 30V, V_{GS}=0V
Gate threshold voltage	$V_{GS\ (th)}$	1.0	–	2.5	V	V_{DS}= 10V, I_D= 1mA
Static drain-source on-state resistance	$R_{DS\ (on)}$*	–	170	240	mΩ	I_D= 1.4A, V_{GS}= 10V
		–	250	350	mΩ	I_D= 1.4A, V_{GS}= 4.5V
		–	270	380	mΩ	I_D= 1.4A, V_{GS}= 4V
Forward transfer admittance	$\|Y_{fs}\|$ *	1	–	–	S	V_{DS}= 10V, I_D= 1.4A
Input capacitance	C_{iss}	–	70	–	pF	V_{DS}= 10V
Output capacitance	C_{oss}	–	15	–	pF	V_{GS}=0V
Reverse transfer capacitance	C_{rss}	–	12	–	pF	f=1MHz
Turn-on delay time	$t_{d\ (on)}$ *	–	6	–	ns	V_{DD}≒ 15V I_D= 0.7A V_{GS}= 10V R_L=21Ω R_G=10Ω
Rise time	t_r *	–	6	–	ns	
Turn-off delay time	$t_{d\ (off)}$ *	–	13	–	ns	
Fall time	t_f *	–	8	–	ns	
Total gate charge	Q_g *	–	1.4	2.0	nC	V_{DD}≒15V R_L=11Ω
Gate-source charge	Q_{gs} *	–	0.6	–	nC	V_{GS}= 5V R_G=10Ω
Gate-drain charge	Q_{gd} *	–	0.3	–	nC	I_D= 1.4A

*Pulsed

●**Body diode characteristics** (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_{SD}	–	–	1.2	V	I_S= 0.6A, V_{GS}=0V

●**Electrical characteristics curves**

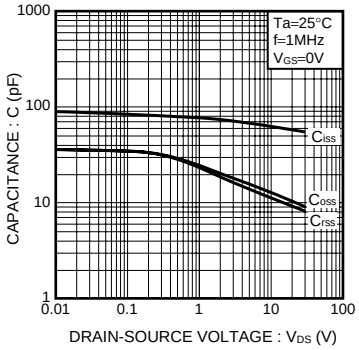


Fig.1 Typical Capacitance vs. Drain-Source Voltage

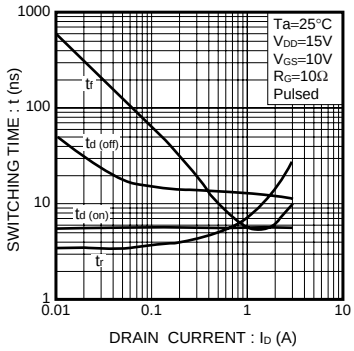


Fig.2 Switching Characteristics

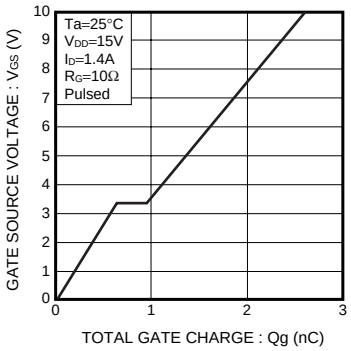


Fig.3 Dynamic Input Characteristics

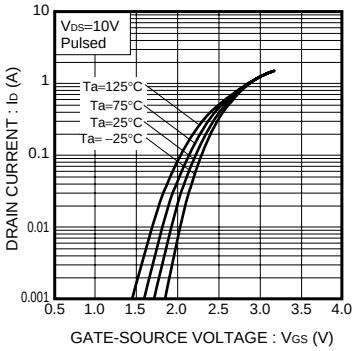


Fig.4 Typical Transfer Characteristics

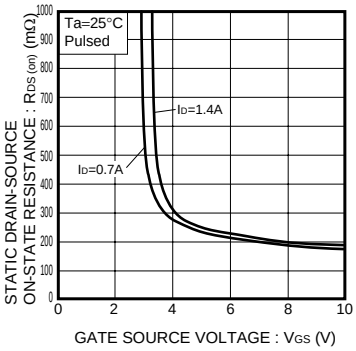


Fig.5 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

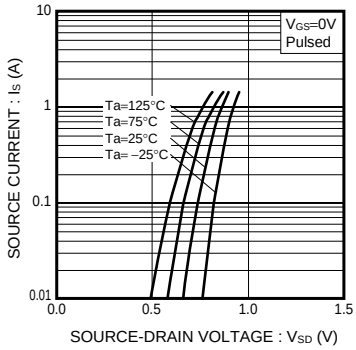


Fig.6 Source Current vs. Source-Drain Voltage

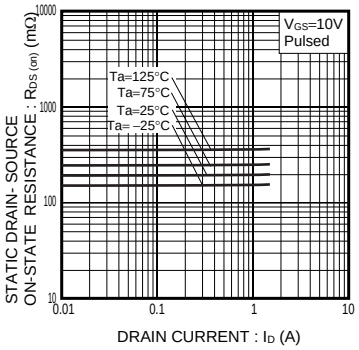


Fig.7 Static Drain-Source On-State Resistance vs. Drain Current (I)

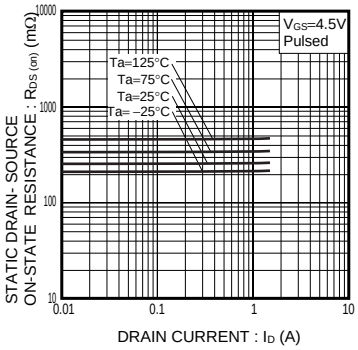


Fig.8 Static Drain-Source On-State Resistance vs. Drain Current (II)

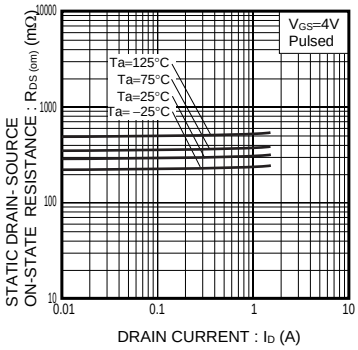


Fig.9 Static Drain-Source On-State Resistance vs. Drain Current (III)

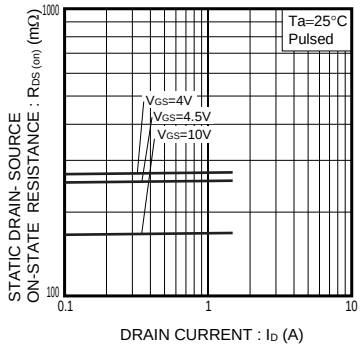


Fig.10 Static Drain-Source On-State Resistance vs. Drain Current (Ⅳ)

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